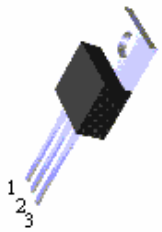
PNP Epitaxial Silicon DarlingtonTransistor

MEDIUM POWER LINEAR SWITCHING APPLICATIONS

- Collector current 10A
- Collector dissipation Pc =75W (Tc = 25℃)

TO-220



Pin : 1. Base
2. Collector
3. Emitter

ORDERING INFORMATION

Device	Operating Temperature	Package
PJP110ACZ	-20℃～+85℃	TO-220

ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	Ic	-10	A
Collector Dissipation	Pc	75	W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55 ~150	℃

ELECTRICAL CHARACTERISTICS (Ta = 25℃)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	Ic = -1mA, I_E = 0	-20			V
Collector-EmitterBreakdown Voltage	BV_{CEO}	Ic = -10mA, I_B =0	-12			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E = -1mA, I_C = 0	-7			V
Collector Cutoff Current	I_{CBO}	V_{CB}= -15V,I_E=0			-100	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}= -3V,I_C=0			-100	μA
DC Current Gain	h_{FE1}	V_{CE}= -3V,I_C=-6A	110			
	h_{FE2}	V_{CE}= -3V,I_C = -10A	90			
Collector-Emitter Saturation Voltage	$V_{CE\ (SAT)}$	I_C= -6A,I_B= -600mA			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE\ (SAT)}$	I_C= -6A, V_{CE}= -4V			-1.5	V

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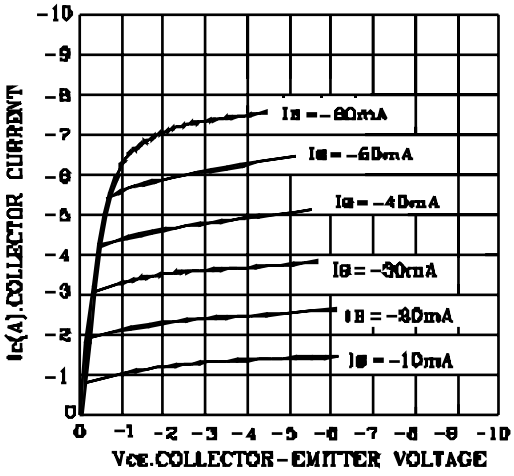
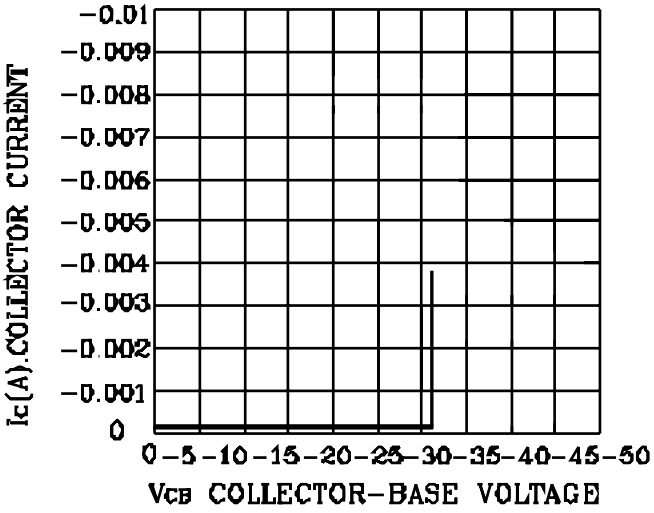
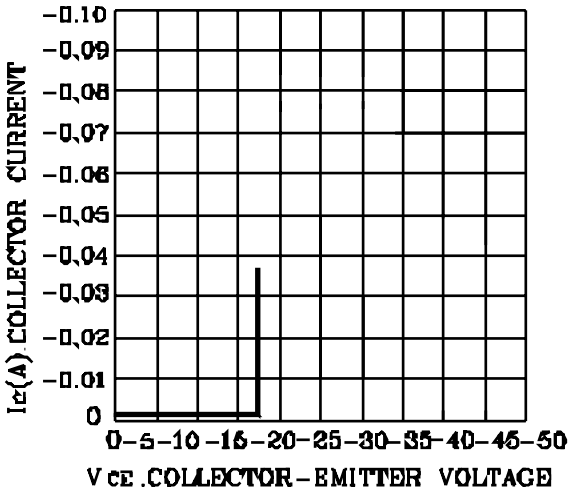
DC CURRENT GAIN



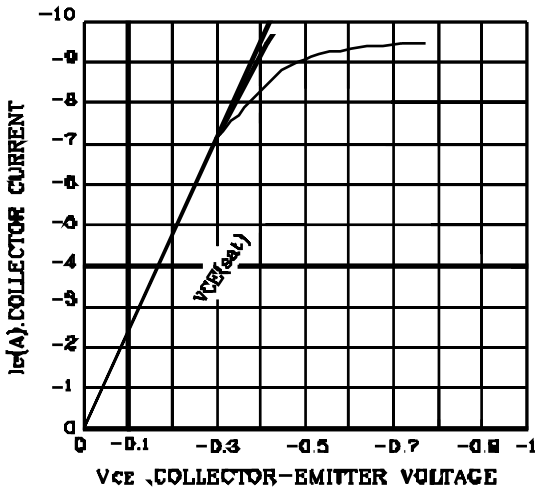
COLLECTOR-BASE BREAKDOWN VOLTAGE



COLLECTOR-EMITTER BREAKDOWN VOLTAGE



COLLECTOR-EMITTER SATURATION VOLTAGE



TO-220 Unit:mm